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**Semiconductor Material:**

Silicon

**Special Features:**

The high power radar transistor device is designed for I-band radar systems operating over the instantaneous bandwidth of 1.210-1.400 ghz, while operating in class c mode this common base device supplies a of 370 watts of peak pulse power

**Shelf Life:**

N/a

**Unit Of Measure:**

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**Demilitarization:**

No

**Fig:**

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